

Serial No. 09/873,674

Attorney Docket No. F0537

**AMENDMENTS****In the claims:**

Please cancel claims ~~15-20~~ without prejudice.

Please amend claim 1 as follows:

1. (Amended) A straddled gate device formed on a semiconductor-on-insulator (SOI) substrate having active regions defined by isolation regions and an insulator layer, the device comprising:

a first gate defining a first channel region interposed between a source and a drain formed within the active region of the SOI substrate;

a second gate straddling the first gate defining second channel regions interposed between the first channel region and the source and the drain; and

a contact connecting the first gate with the second gate.

Marked-up versions of the amended claim appear in an Appendix A.

Please add claim 21 as follows:

21. (Added) The straddled gate device according to claim 1, wherein when the device is in an off state ( $I_{off}$ ), an effective channel length is defined by the first gate and the second gate, and when the device is in the on state ( $I_{on}$ ), the effective channel length is defined by the first gate.

**REMARKS**

Following entry of this amendment, claims 1-14 and 21 will be pending. Claims 15-20 have been canceled. Claim 1 has been amended to remove language which may have been vague and indefinite. Additionally, claim 21 has been added. The Applicants have enclosed in an Appendix B a complete set of claims for the Examiner's convenience.